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| Form PTO 1449 (Modified) | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | ATTY DOCKET NO. 205109US20DIV | | SERIAL NO. 09/822,335 | |
| LIST OF REFERENCES CITED BY APPLICANT | | | | APPLICANT Paul M. ENQUIST | | | |
| | | | | FILING DATE RCE Filed July 24, 2003 | | GROUP 2814 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| <i>W</i> | AA | 5,841,197 | 11/1998 | Adamic, Jr. | <i>11</i> | <i>11</i> | |
| <i>W</i> | AB | 5,185,274 | 02/1993 | Chang et al. | <i>11</i> | <i>11</i> | |
| <i>W</i> | AC | 5,296,390 | 03/1994 | Awano | <i>11</i> | <i>11</i> | |
| <i>W</i> | AD | 5,504,359 | 04/1996 | Rodder | <i>11</i> | <i>11</i> | |
| | AE | | | | | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
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| OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.) | | | | | | | |
| <i>W</i> | AR | Submicron Lateral Scaling of Vertical-Transport Devices: Transferred-Substrate Bipolar Transistors and Schottky-Collector Tunnel Diodes; M. Rodwell et al.; Invited Paper, 1997 OSA Ultrafast Electronics and Optoelectronics Conference | | | | | |
| <i>W</i> | AS | A 277-GHz F_{max} Transferred-Substrate Heterojunction Bipolar Transistor; B. Agarwal et al.; IEEE Electron Device Letters, Vol. 18, No. 5, May 1997, pgs. 228-231 | | | | | |
| <i>W</i> | AT | Transferred Substrate Schottky-Collector Heterojunction Bipolar Transistors: First Results and Scaling Laws for High F_{max} ; U. Bhattacharya, et al.; IEEE Electron Device Letters, Vol. 16, No. 8, August 1995, pgs. 357, 359 | | | | | |
| <i>W</i> | AU | A > 400 Ghz F_{max} Transferred-Substrate HBT Integrated Circuit Technology; R. Pullala et al.; DRC 1997 | | | | | |
| <i>W</i> | AV | Deep Submicron Transferred-Substrate Heterojunction Bipolar Transistors; Q. Lee et al.; DRC 1998 | | | | | |
| <i>W</i> | AW | 170 GHz Transferred-Substrate Heterojunction Bipolar Transistor; U. Bhattacharya et al.; Electronics Letters, 18 th July 1996, vol. 32, No. 15, pgs. 1405-6 | | | | | |
| <i>W</i> | AX | Transferred Substrate Heterojunction Bipolar Transistors; Dissertation by U. Bhattacharya, Nov. 27, 1996 | | | | | |
| <i>W</i> | AY | Digital Integrated Circuits in the Transferred-Substrate HBT Technology, Dissertation by R. Pullala, June 1998 | | | | | |
| | AZ | | | | | | <input type="checkbox"/> Additional References sheet(s) attached |
| Examiner <i>Mjm</i> <i>W</i> <i>Mj</i> | | | | | Date Considered <i>7-8-04</i> | | |
| *Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |